P-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

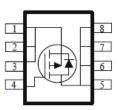
Typical Applications:

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-30	8 @ V _{GS} = -10V	-18	
	11 @ V _{GS} = -4.5V	-15	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			-30	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _A =25°C	I-	-18				
Continuous Diam Curient	T _A =70°C	I _D	-13	Α			
Pulsed Drain Current ^b	I_{DM}	-50					
Continuous Source Current (Diode Conduction) a		I _S	-4.6	Α			
Power Dissipation ^a	T _A =25°C		3.5	W			
rower Dissipation	T _A =70°C	' D	2	VV			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
IMAXIMUM Sunction-to-Ambient	Steady State	IΛθJA	81	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

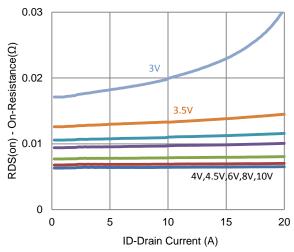
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-25			Α	
Dunin Course On Braintana a	r	$V_{GS} = -10 \text{ V}, I_D = -13.6 \text{ A}$			8	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -10.9 \text{ A}$			11	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -13.6 \text{ A}$		12		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$		-0.76		V	
_		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		60		nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -13 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -13.6 \text{ A}$		17			
Gate-Drain Charge	Q_{gd}	1 _D = -13.0 A		22			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -15 \text{ V}, R_1 = 1.2 \Omega,$		14			
Rise Time	t _r	$V_{DS} = -13 \text{ V}, K_L - 1.2 \Omega,$ $I_D = -13.6 \text{ A},$		37		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		124		ns	
Fall Time	t _f	V GEN = 10 V, 11 GEN = 0 12		55			
Input Capacitance	C _{iss}			5743			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		453		pF	
Reverse Transfer Capacitance	C_{rss}			446			

Notes

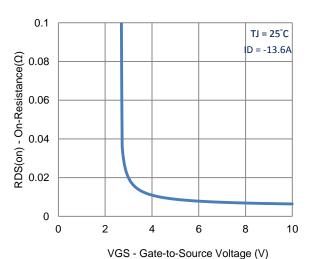
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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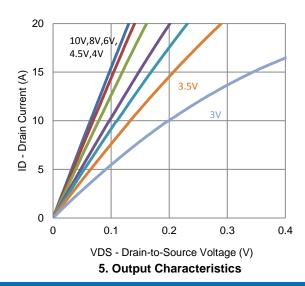
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

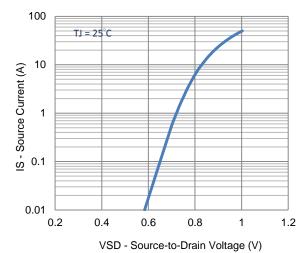


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TJ = 25°C

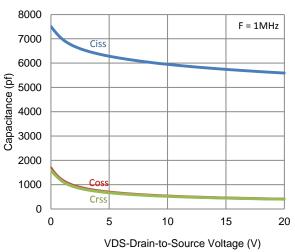
(Y) tuend 10
0 0 1 2 3 4 5

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



6. Capacitance

Typical Electrical Characteristics

2

1.5

0.5

-50

-25

0

25

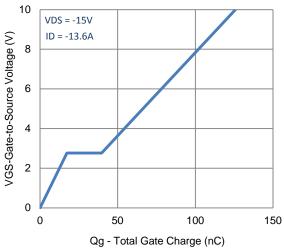
50

75

100

125

150

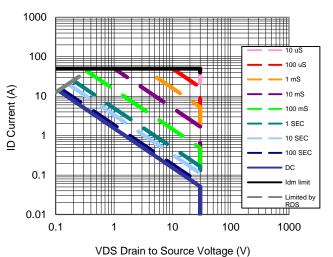


Total Gate Charge (nC) TJ -JunctionTemperature(°C)

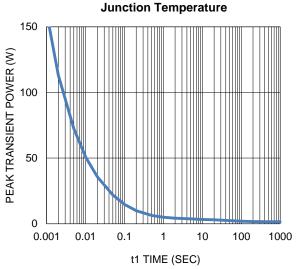
7. Gate Charge

8. Normalized On-Resistance Vs

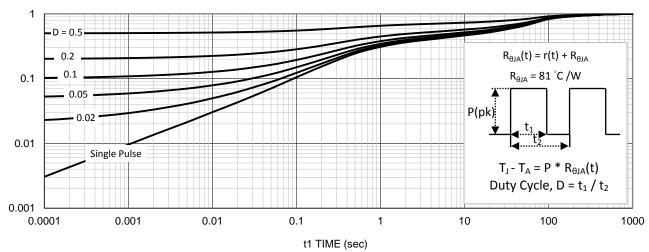
 $RDS(on) - On-Resistance(\Omega)$ (Normalized)



9. Safe Operating Area

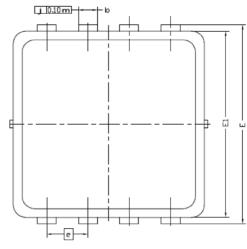


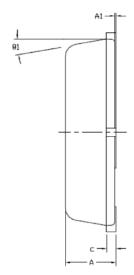
10. Single Pulse Maximum Power Dissipation

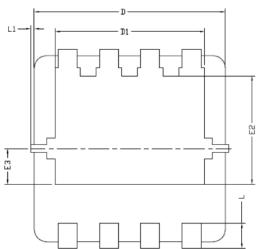


11. Normalized Thermal Transient Junction to Ambient

Package Information







птм	MILLIMETERS			INCHES			
DIM,	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0,0315	0,0354	
A1	0.00		0,05	0,000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.35 BSC			0.093 BSC			
Ε	(3	3.20 BSC			0.126 BSC		
E1	3	3'00 B2C			0.118 BSC		
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0.65 BSC			0.026 BSC			
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0,004	
91	0°	10°	12°	0°	10°	12°	